

Application No.: 10/754,518

**AMENDMENT TO THE CLAIMS**

1. (Currently amended) A semiconductor substrate having a notch in an edge portion thereof,

the notch having two shoulder portions each configured as an arc and a difference in curvature between the two shoulder portions being not less than 0 mm and not more than 0.1 mm, wherein each of the two shoulder portions has a curvature not less than 0.3 mm and not more than 2.0 mm.

2. (Canceled)

2. 3. (Currently amended) The semiconductor substrate of claim 1, wherein the notch has a bottom portion configured as an arc and the bottom portion has a curvature not less than 1 mm and not more than 1.5 mm.

3. 4. (Currently amended) The semiconductor substrate of claim [[3]] 1, wherein the notch has two wall surfaces each mirror-finished and forming an angle not less than 89° and not more than 95° therebetween.

5. (Withdrawn) A method for fabricating a semiconductor device using a semiconductor substrate as recited in claim 1, the method comprising the steps of:

burying an insulating film ~~or a conductive film~~ in a depressed portion provided in the semiconductor substrate; and

~~planarizing the insulating film or the conductive film by chemical mechanical polishing.~~

**Application No.: 10/754,518**

6. (Withdrawn) A method for fabricating a semiconductor device using a semiconductor substrate as recited in claim 1, the method comprising the steps of:

forming an end-point detection film on the semiconductor substrate;  
performing etching with respect to the end-point detection film and the semiconductor substrate by using a mask pattern to form an isolation trench;  
burying an insulating film in the isolation trench; and  
planarizing the insulating film by chemical mechanical polishing.

7. (Withdrawn) The method of claim 6, wherein a polishing speed for the insulating film is double or more a polishing speed for the end-point detection film in the step of planarizing the insulating film.

8. (Withdrawn) The method of claim 6, further comprising, after the step of planarizing the insulating film, the step of:

polishing the end-point detection film by chemical mechanical polishing.

9. (Currently amended) A method for fabricating a semiconductor substrate having a notch in an edge portion thereof, the method comprising the step of:

a processing step of mirror-polishing the edge portion, the processing step including the step of shaping each of two shoulder portions of the notch into an arc and adjusting a difference in curvature between the two shoulder portions to a value not less than 0 mm and not more than 0.1 mm, wherein the processing step includes the step of adjusting the curvature of each of the two shoulder portions to 0.3 mm or more and 2.0 mm or less.

Application No.: 10/754,518

10. (Canceled)

~~5~~ 11. (Currently amended) The method of claim ~~9~~<sup>4</sup>, wherein the processing step includes the step of shaping a bottom portion of the notch into an arc and adjusting a curvature of the bottom portion to 1 mm or more and 1.5 mm or less.

~~6~~ 12. (Currently amended) The method of claim ~~[[11]] 9~~<sup>4</sup>, wherein the processing step includes the step of mirror-finishing two wall surfaces of the notch to form an angle not less than 89° and not more than 95° therebetween.